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**Mind is the first defence**

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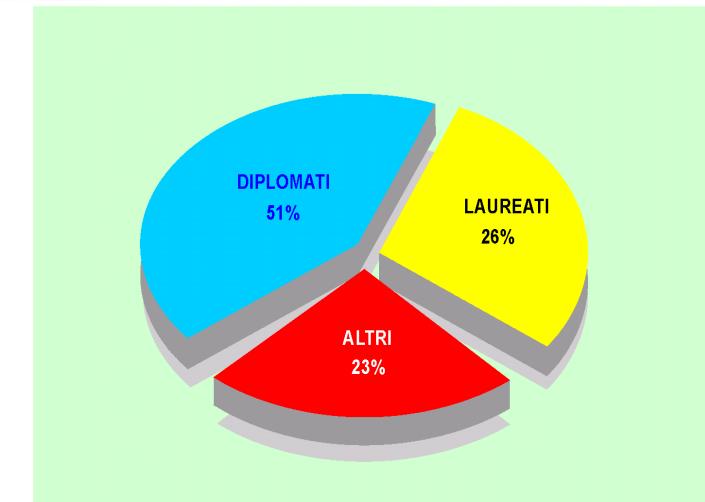
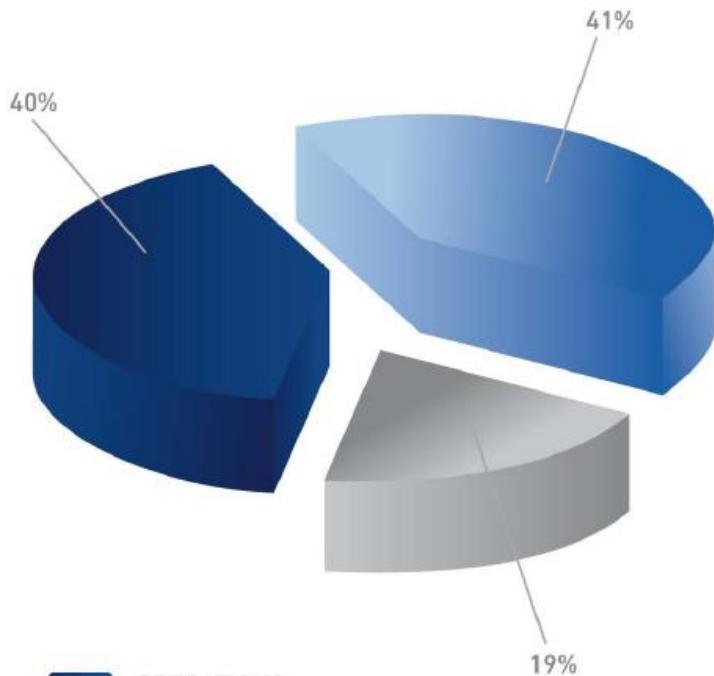


**Principali prodotti:**

- ✓ sistemi ESM (Electronic Support Measures)
- ✓ sistemi SIGINT (Signal INTElligence)
- ✓ sistemi ECM (Electronic Counter Measures)



# ELETTRONICA PERSONNEL



# Argomenti

## ■ I sistemi ELT- ESM

- ◆ RWR (WO wide open receiver)
- ◆ SIGINT/ELINT (SH super-het receiver)

## ■ I sistemi ELT - ECM+ESM

- ◆ Phased Arrays
- ◆ Down-Up converters

## ■ La progettazione microonde in ELT

- ◆ Flusso di PROGETTO
- ◆ Criticità & tecnologie
- ◆ Esempio

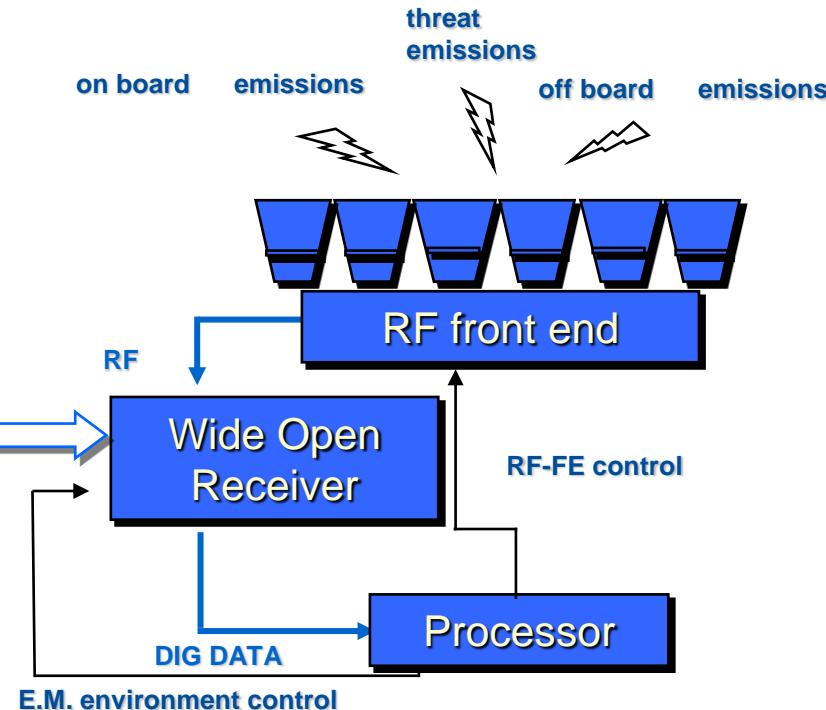
## ■ Le tecnologie microonde in ELT

# Receiver architecture vs E.M. scenario and mission:

## Wide Open Rx (ESM/RWR)

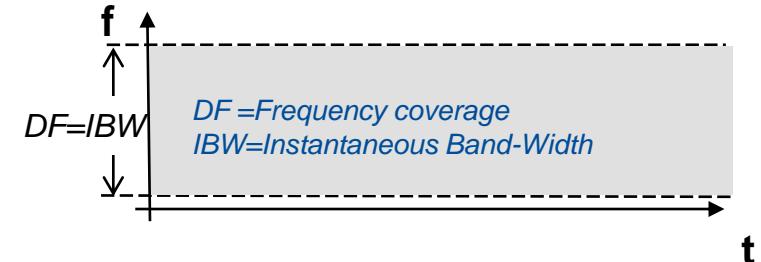
### RWR & HPOI - SURVEILLANCE

- Full instantaneous band
- Instantaneous Inhibition on the interfering signal (CW)
- Fast response time
- Medium sensitivity -60 dBm
- AOA of mainbeam (up to HADF\*)
- Emission analysis, mode determination
- Emitter identification



\*HADF, High Accuracy Direction Finding better than 1-2° RMS

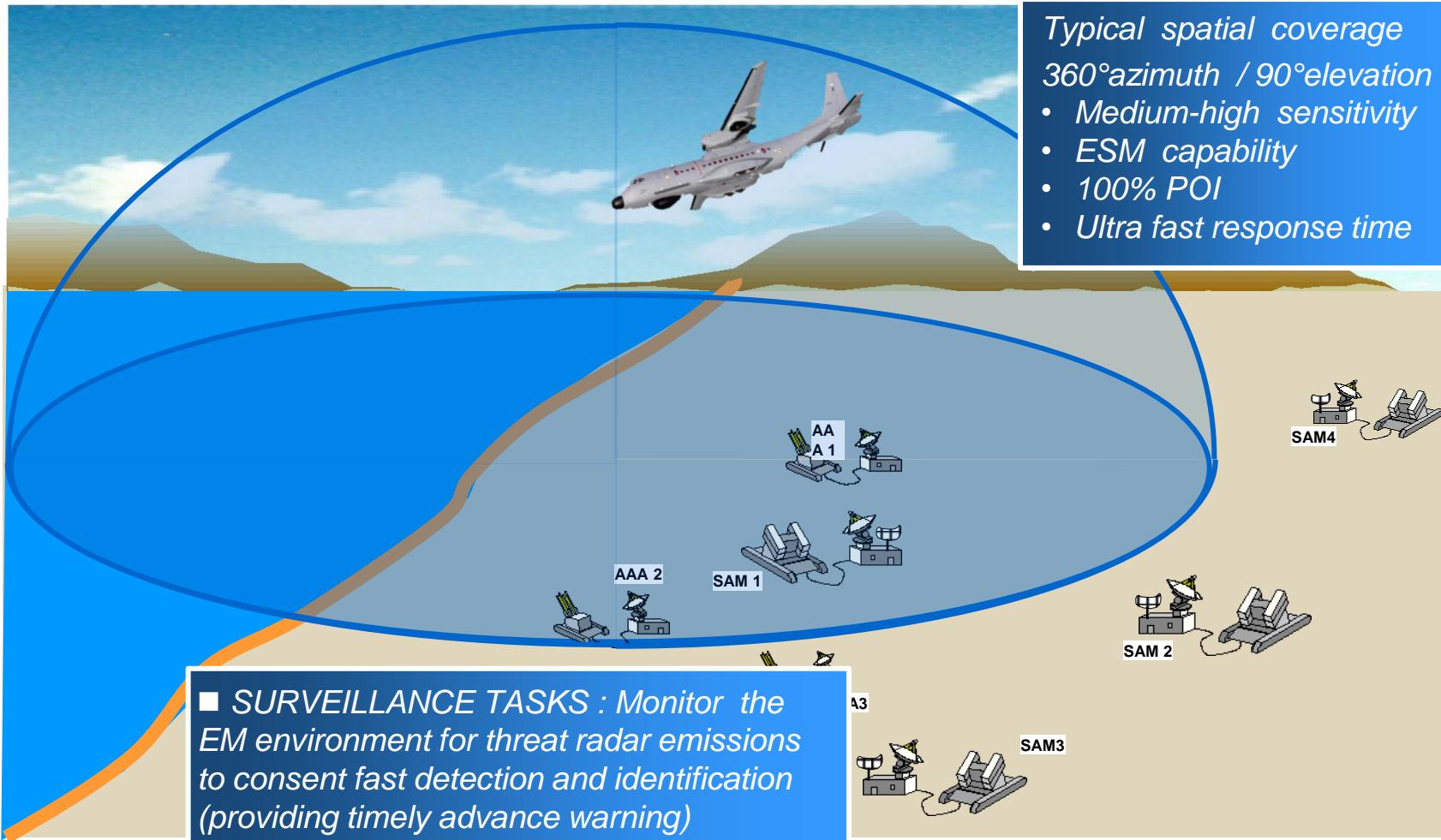
- **Platforms:** naval, airborne (large/medium body, tactical A/C), ground station & mobile vehicle
- **Missions:** patrolling, coastal surveillance, SAR (mainly utility helo & cargo), light combat



### Missions requirements:

- threat alarm & avoidance, even in partially unknown scenario
- Surveillance, aid to situation awareness
- Electronic Reconnaissance
- ECM designation (if any)
- Emitter recording

# HPOI Receiver spatial coverage

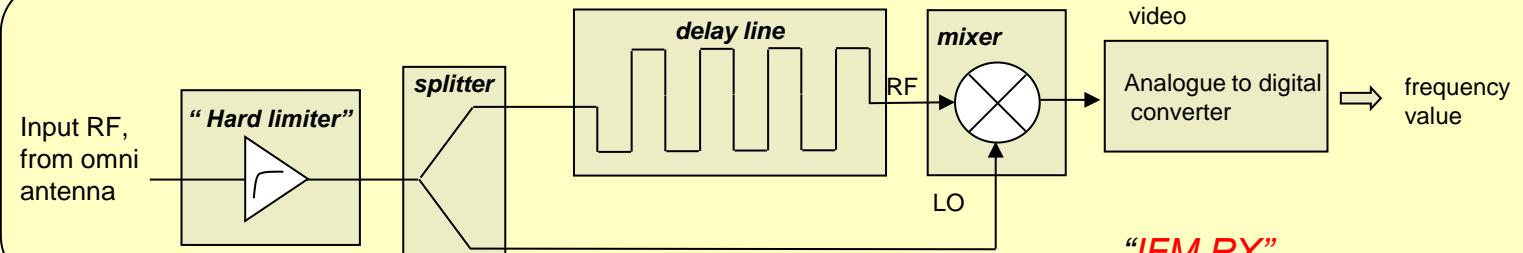


**POI**  
Probability of intercept

# The WO analogue receiver: full band IFM Rx plus AM Crystal Video Rx

The EW analogue RX is typically based on an single-channel IFM (Instantaneous frequency measurement) receiver with a multi- channel crystal video-envelope detector providing Amplitude monopulse Direction finding

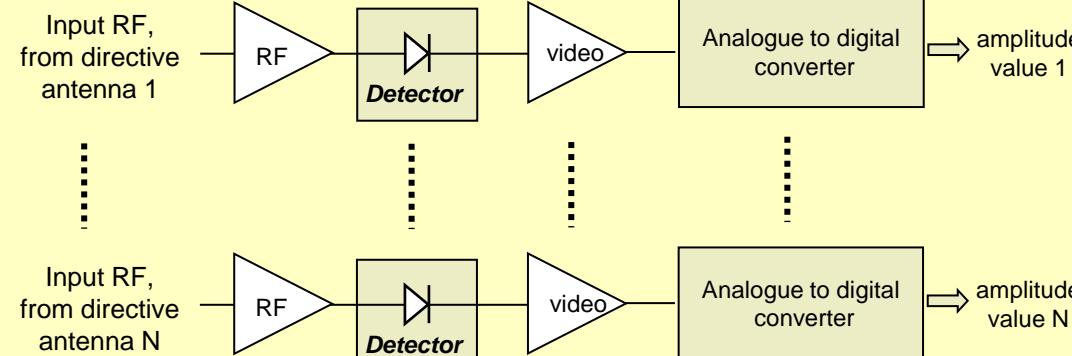
- Relatively poor sensitivity
- Cannot sort simultaneous signals



**“IFM RX”**

- Simple,
- (relatively) inexpensive,
- instantaneous,
- High Probability of Intercept (POI) in frequency range

**“WIDE OPEN RX”**

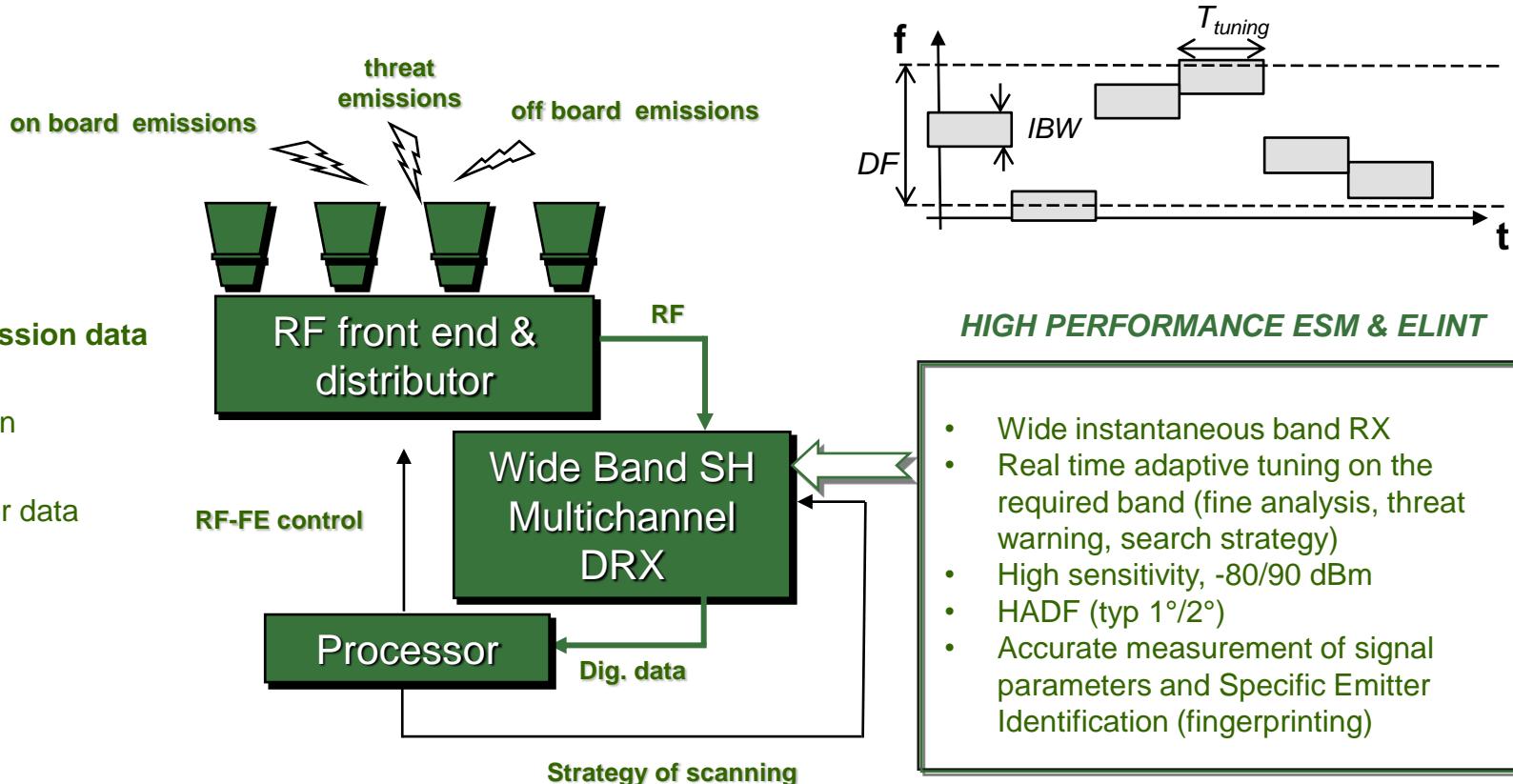


Amplitude  
Angle of  
Arrival ,  
PW,TOA

- Poor sensitivity and simultaneous signal performance
- Special design for CW is required

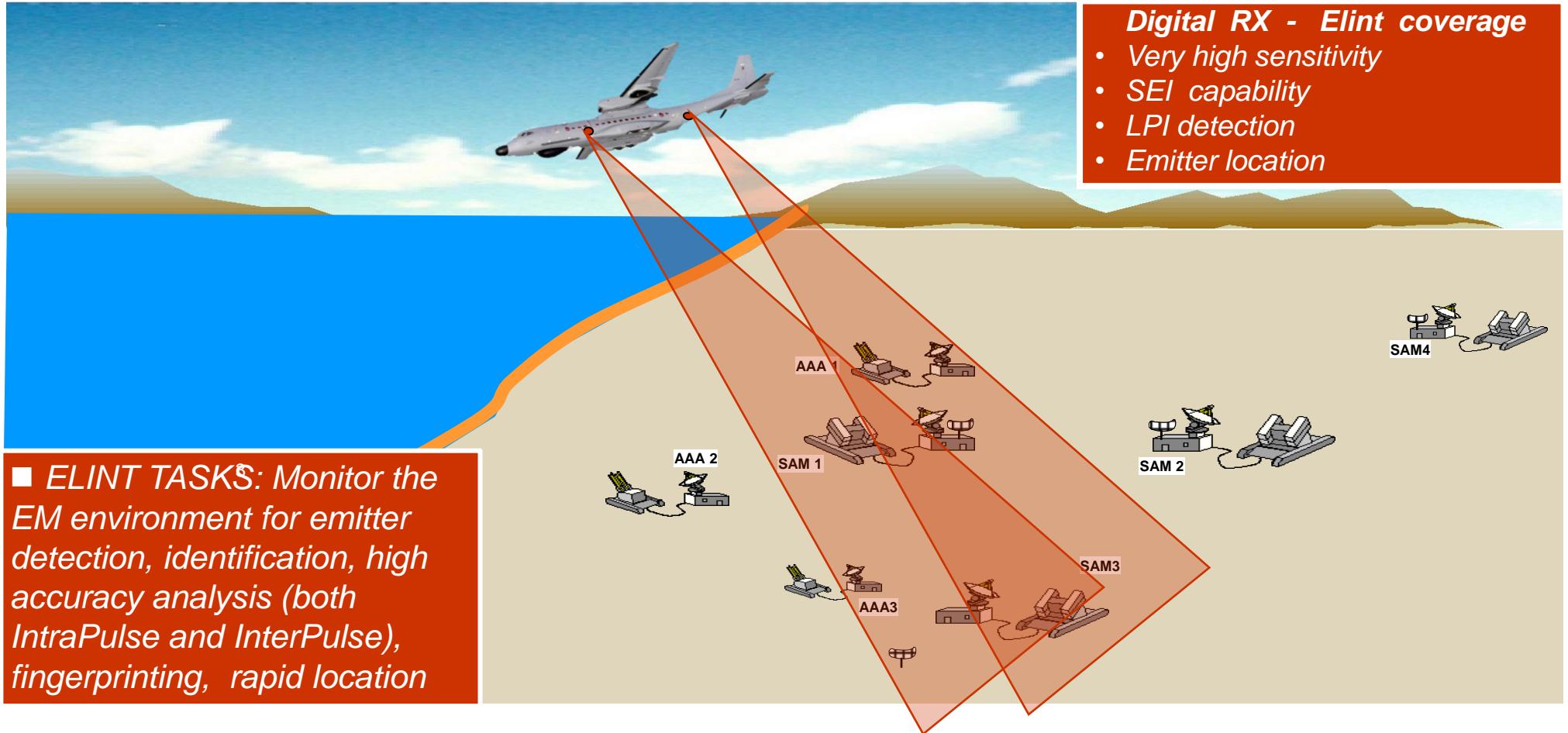
**“Crystal video RX”**

# *Receiver architecture vs E.M. scenario and mission: Wide Band SH DRX (ESM/ELINT)*



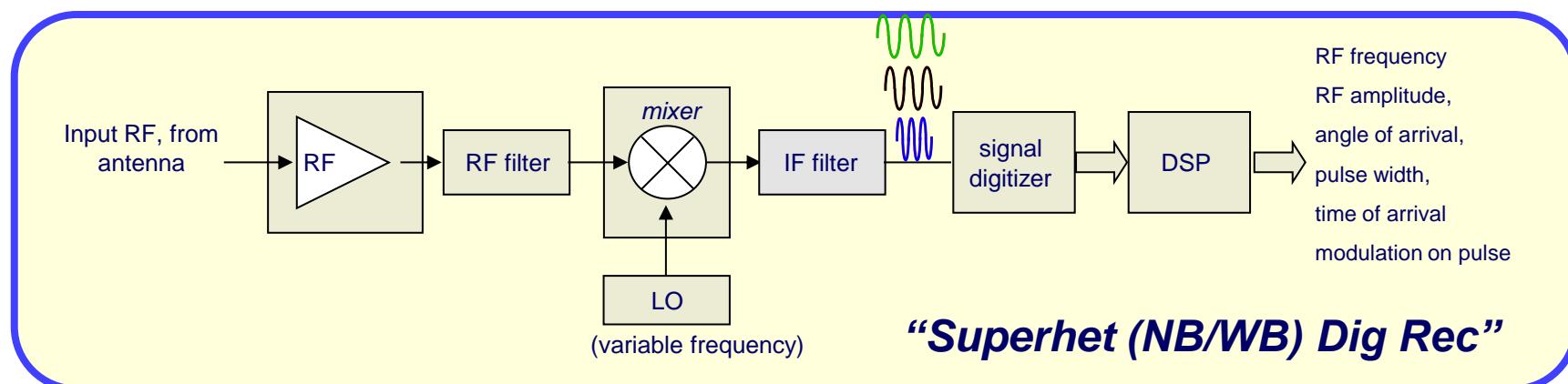
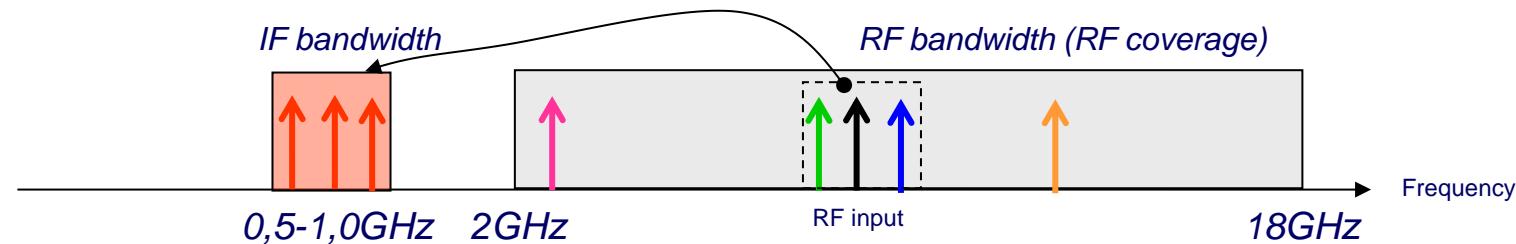
**Platform & mission :** ELINT/SIGINT naval, airborne (large/medium body) and ground fixed-mobile stations

# SH Digital Receiver spatial coverage



# The “Superhet” narrow/wide band digital receiver

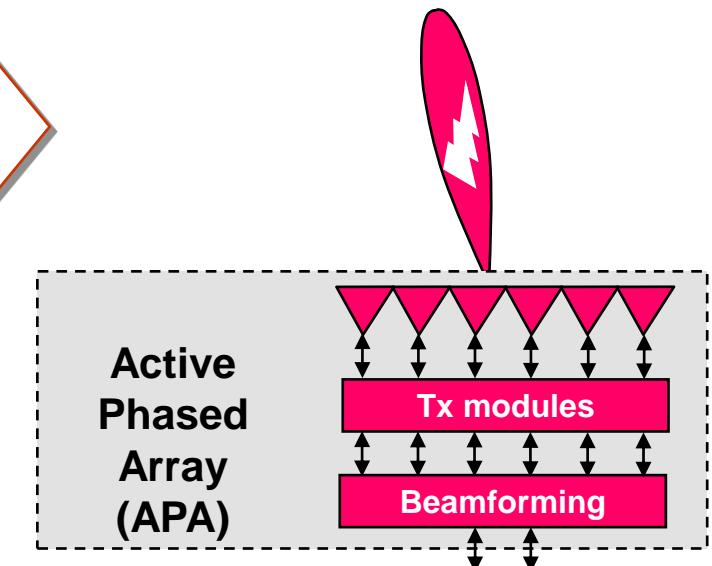
The **superheterodyne receiver** uses frequency mixing to convert a received BW of signal to a fixed lower frequency bandwidth, which can be conveniently sampled and processed using fully digital techniques



# Advantages of Solid State transmitter technology - ECM

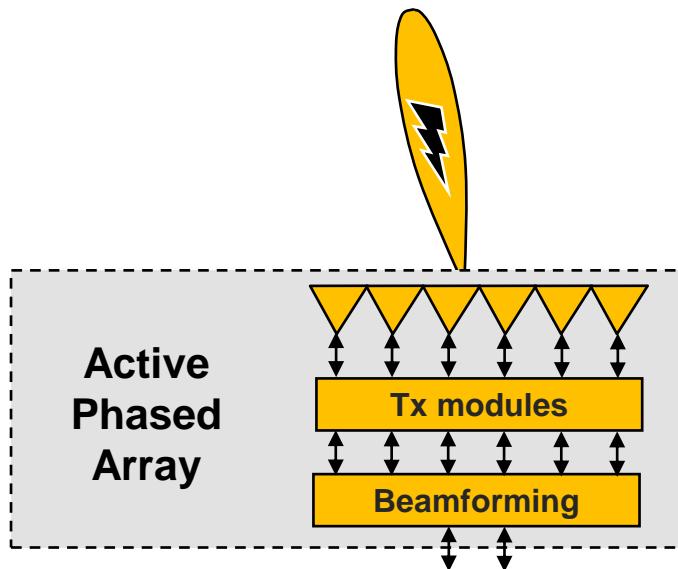
- **Very high ERP (Effective radiated power):**
  - 100% duty cycle with ERP fine control
  - Capability to counter high peak power pulse as well as complex signals
- **Very large space coverage achieved by a single APA :**
  - single-aperture AND multiple-aperture
- **Very High ECM availability & Readiness:**
  - graceful array degradation, no warm up time
- **Full equipment compatibility:**
  - focused energy, low side lobes, predictable jamming
  - Low level of radiated power
- **Maintainability benefits:**
  - no High Voltage Power Supply; high Mean Time Between Failure
- **High ECM effectiveness and efficiency**
  - Multiple and different type of simultaneous threat (CW / pulse / pulse Doppler; simultaneous or very high fast time multiplexing)
  - Low weight & power consumption

*Solid state transmitter benefits related with the Active Phased Array architecture*



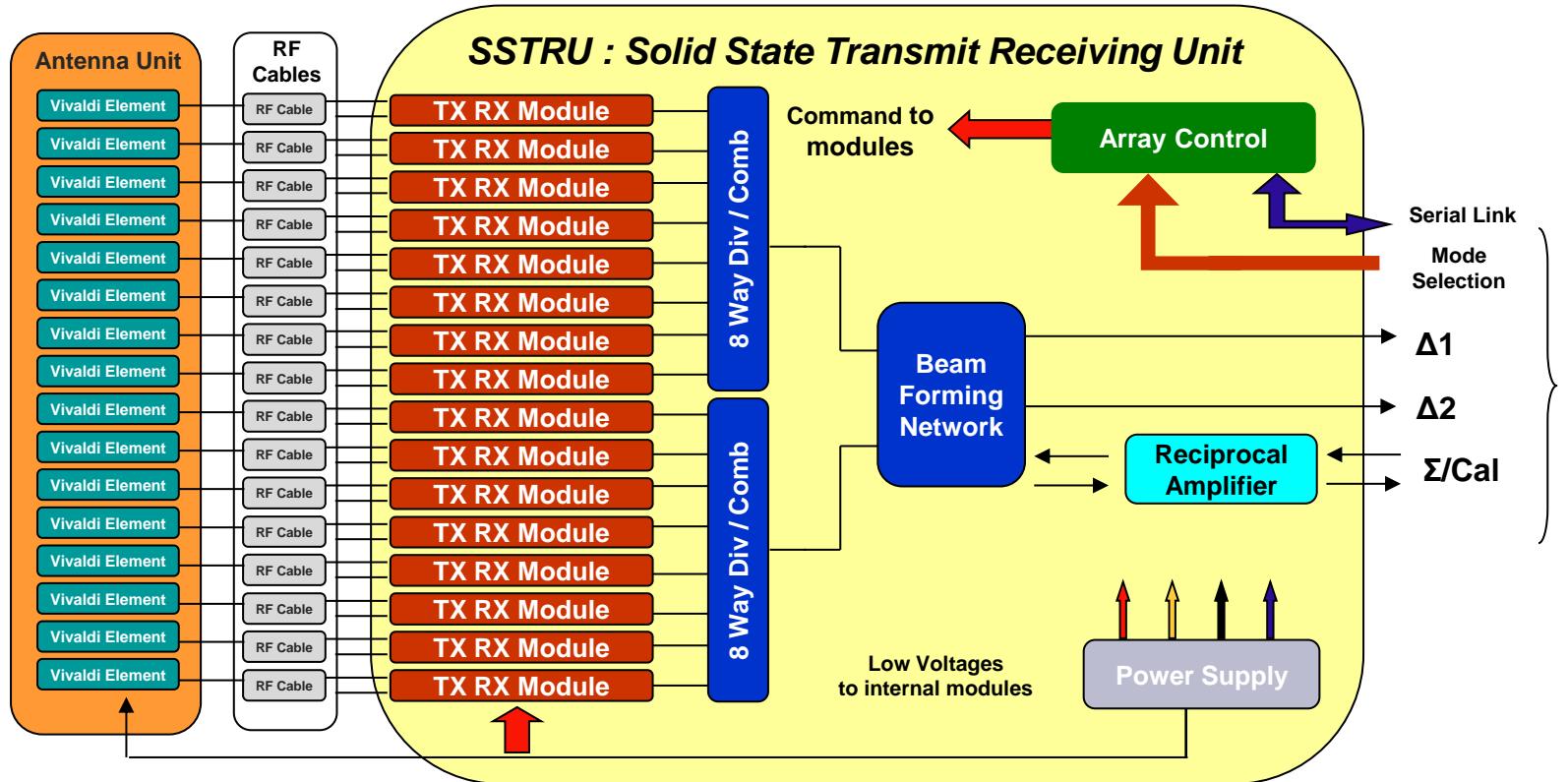
# Advantages of high gain - ESM receiver technology

ESM receiver benefits related with the Active Phased Array high gain receiving architecture



- **Very high DOA Accuracy (typ <1° RMS degree depending on installation):**
  - both in azimuth and elevation (planar APA) , narrow beam **mono-pulse measurement (phase or amplitude)**
  - better Situation Awareness
- **High ECM/ESM sensitivity:**
  - long range detection
- **Flexibility :**
  - Stand-alone operation
  - Designated by a low performance RWR
  - Self-pointing and self-stabilizing

# APA functional scheme

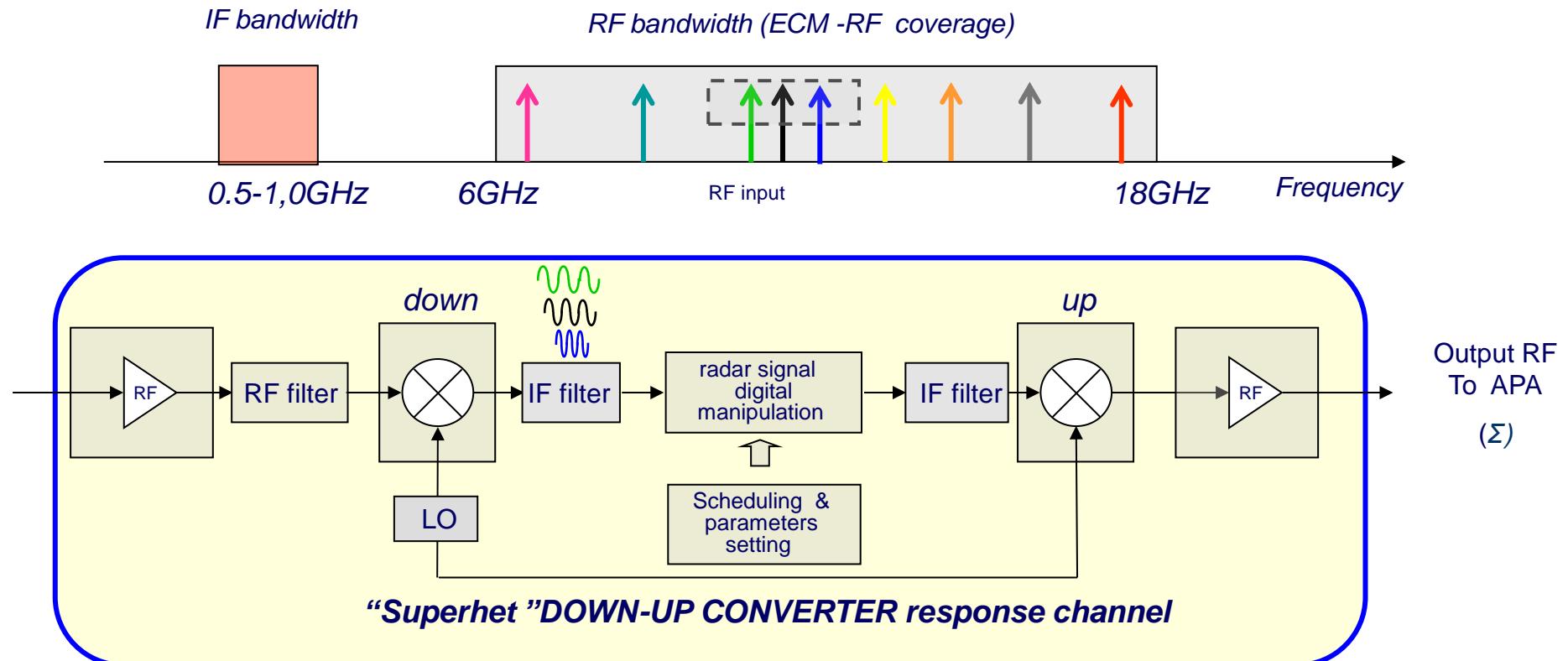


In modalità TX, il segnale è proventinato dal D.U.C e inviato al connettore  $\Sigma$

In modalità RX, il segnale da inviare al D.U.C viene prelevato dai connettori  $\Delta 1$  e  $\Delta 2$

# The “superhet” response channel architecture

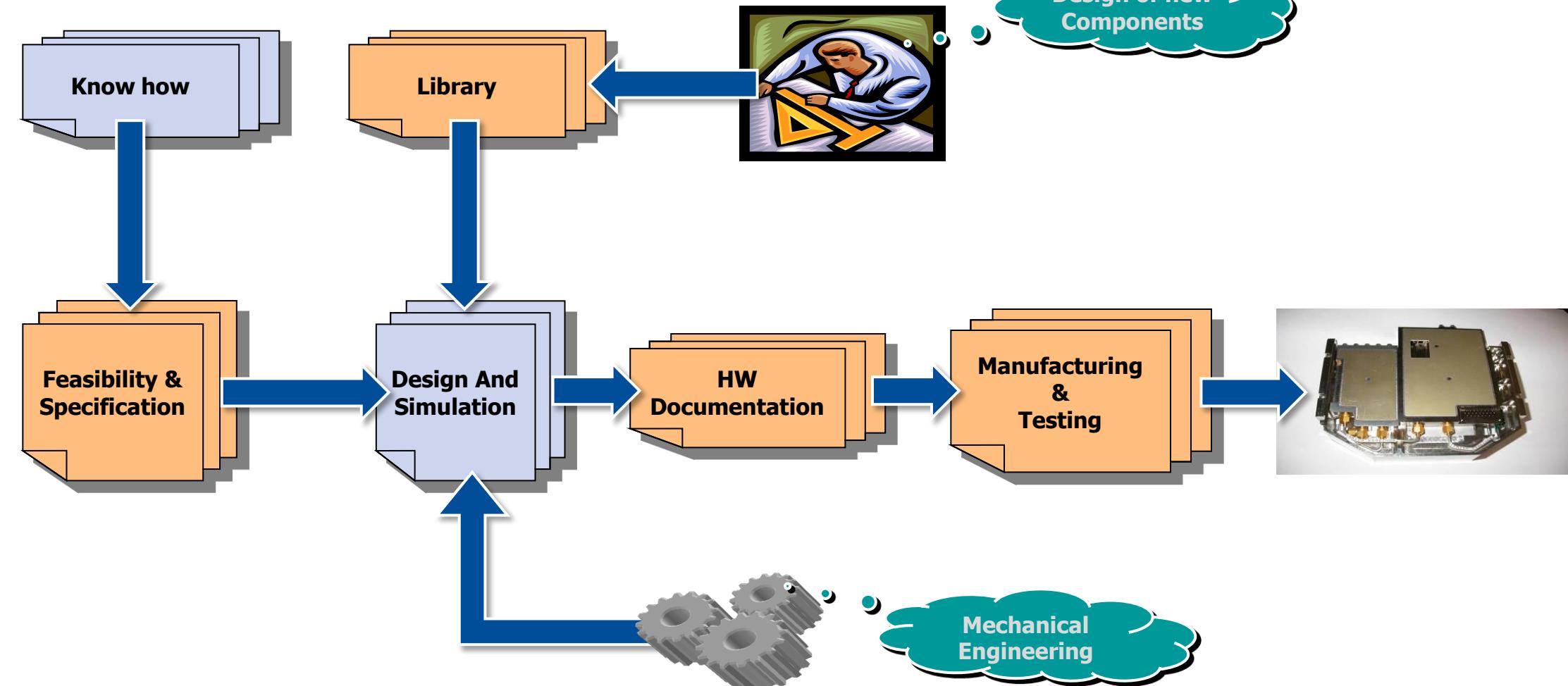
The superheterodyne selective receiver is the basic response channel architecture in any jammer system where a narrow band of signal has to be handled at time for jamming purpose



# PROGETTAZIONE MW ELT

- Flusso di PROGETTO
- Principali criticità & tecnologie
- Esempio di progetto HW

# HW Design Flow



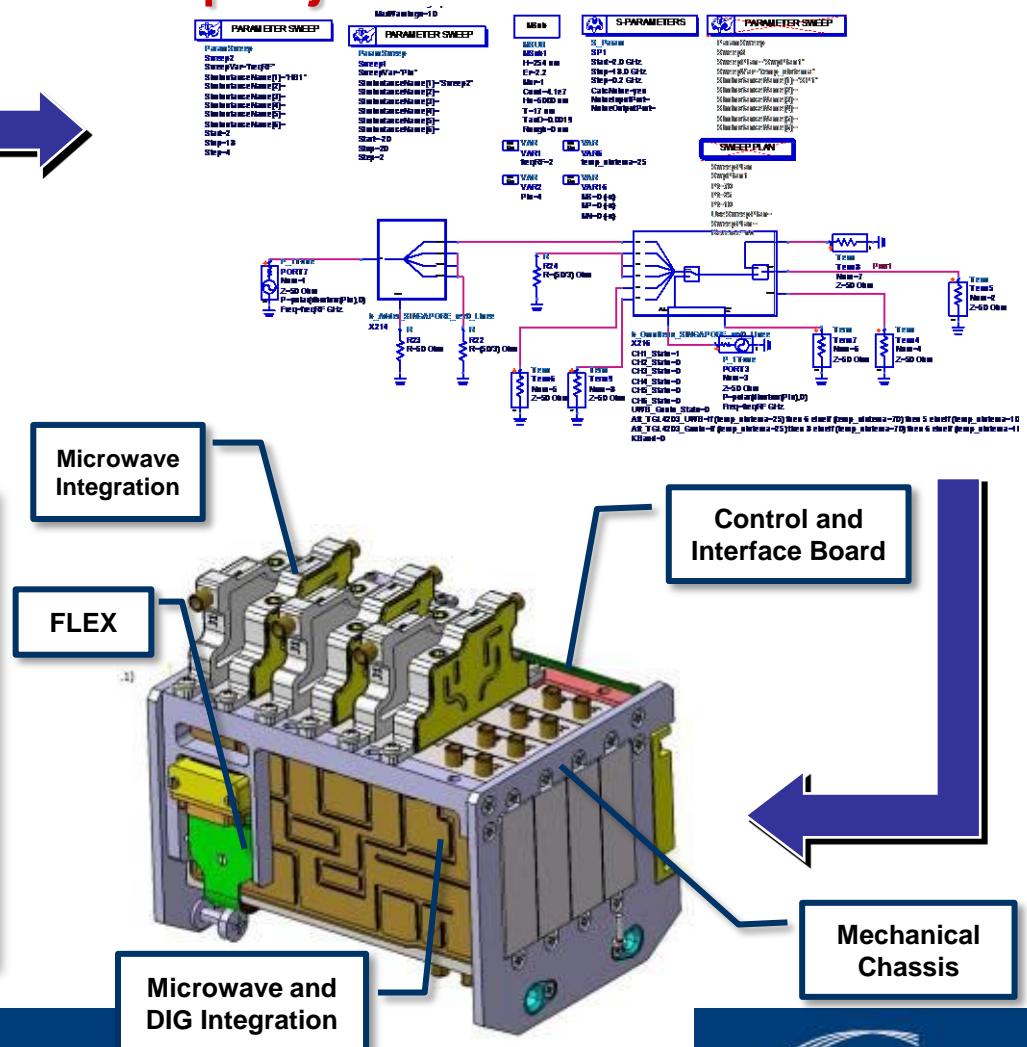
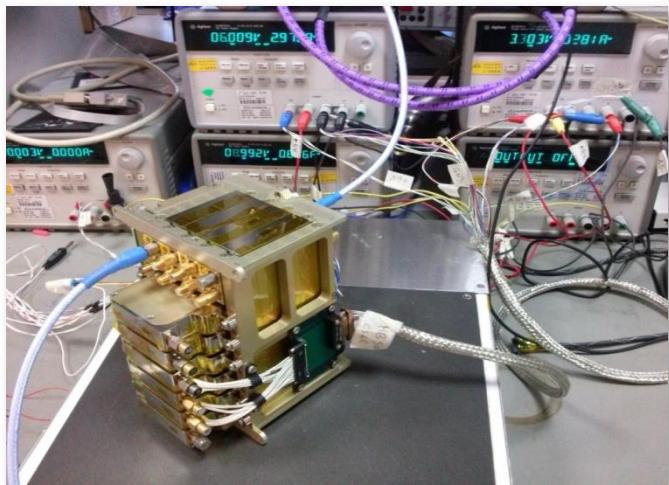
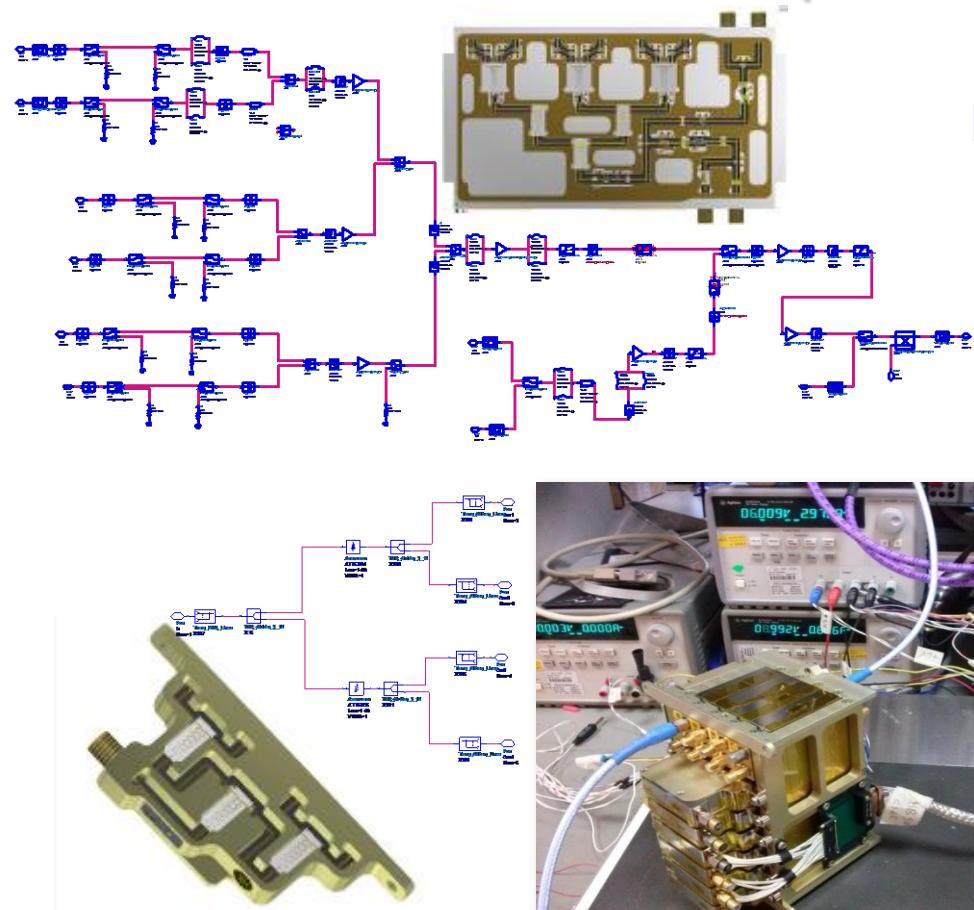
### ***Critical Design Constraints:***

- ***High levels of HW integration  
(RF&Digital)***
- ***Time To Market***
- ***Thermal and mechanical issues***
- ***Technological upgrading***
- ***Integration in company internal design  
flow***

### ***Microwave Technologies:***

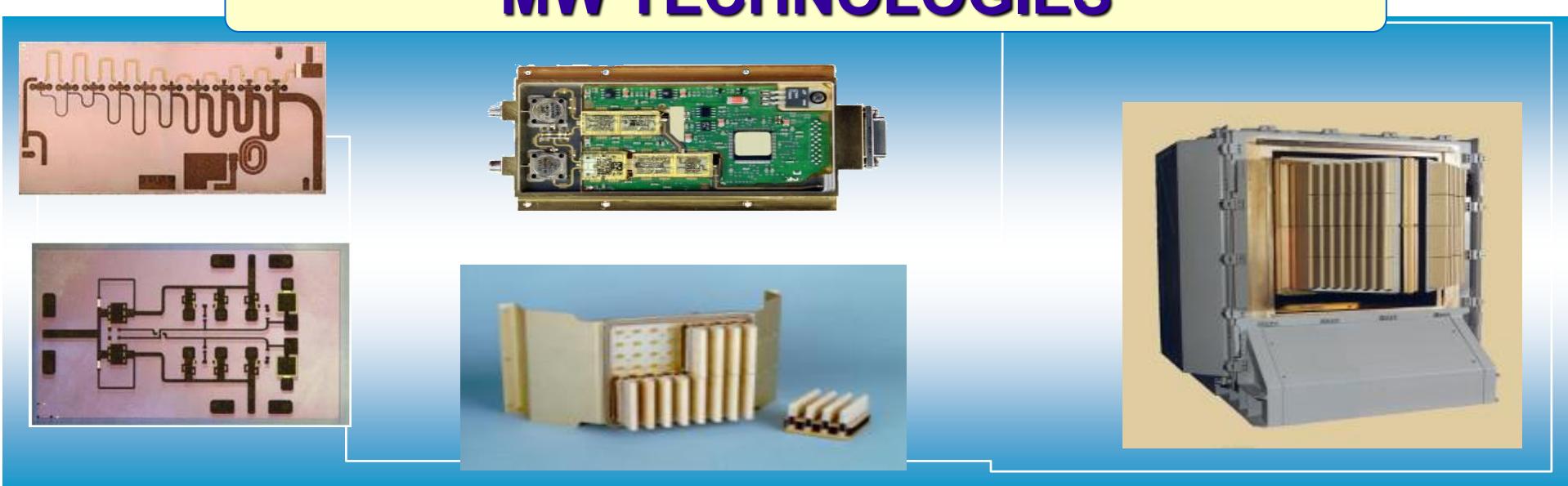
- ***GaAs Monolithic microwave circuits (ELT  
design)***
- ***GaN on SiC Monolithic microwave circuits***
- ***Multilayer video/digital circuits***
- ***Thin Film on alumina and teflon glass  
substrates***
- ***Assembling processes***
- ***M.M.C.M (Microwave Multi -Chip Module)***

# Example of hierarchical project

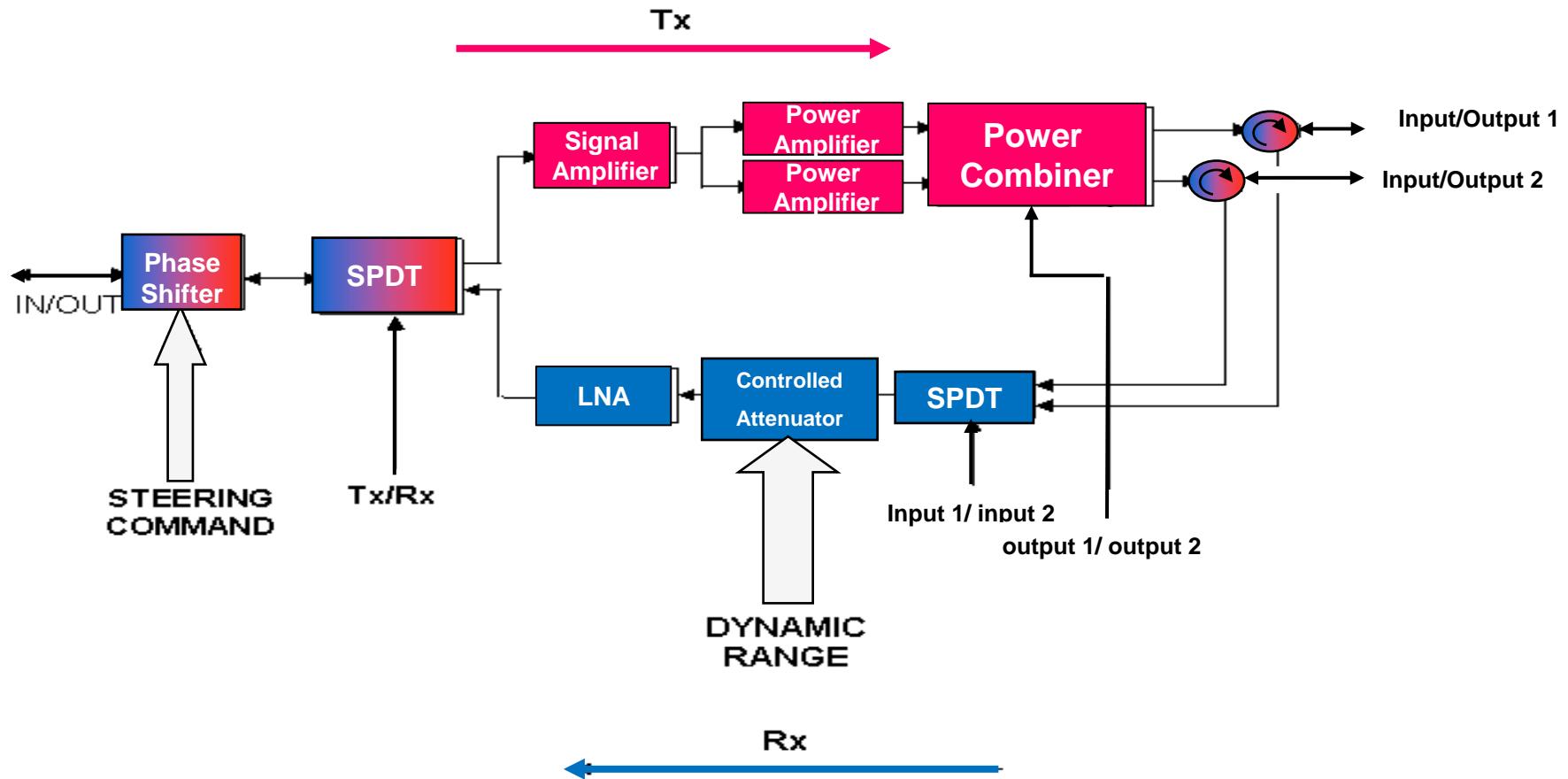




## MW TECHNOLOGIES



# Classic T/R module architecture (dual I/O)



# Tx/Rx MODULE ROAD MAP



1993  
Pout 0.5 W



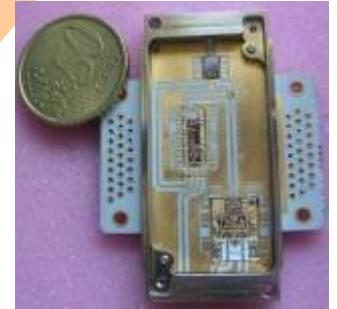
1997  
Pout 1.0 W



2001  
Pout 4.0 W



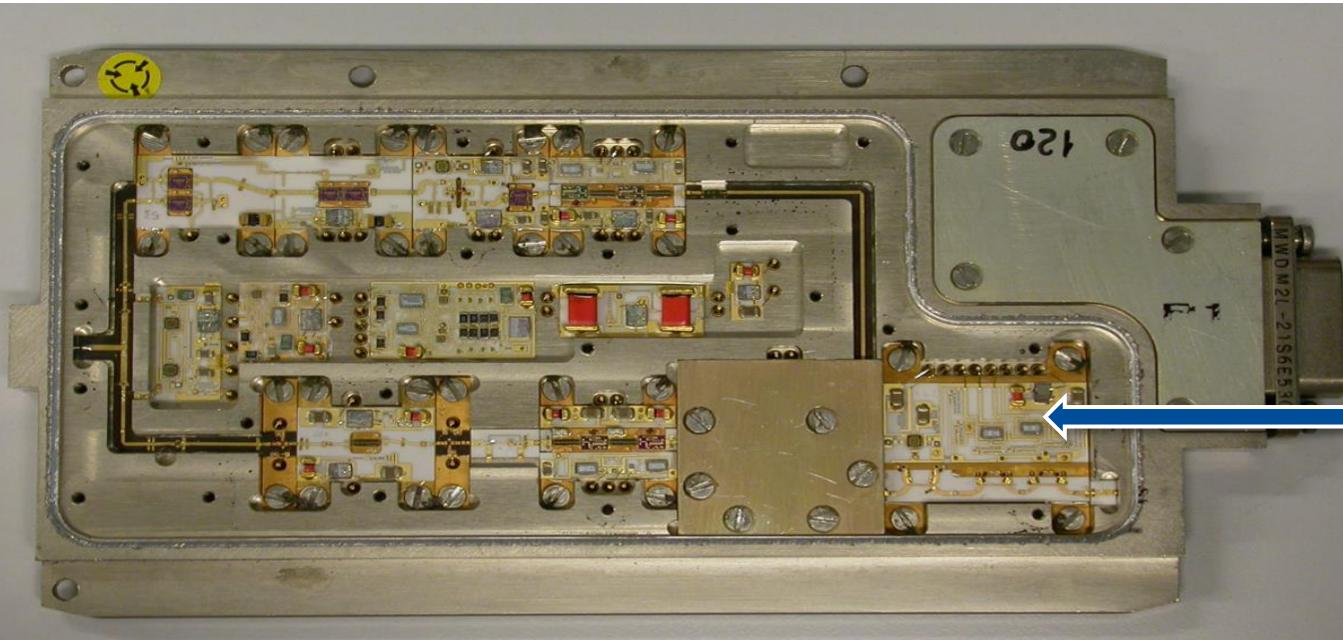
2009  
Pout 4.0 W



2012  
Pout 8.0 W

# Tx/Rx 1° Generation

## TXRX 1Watt RFout - Avionic Application

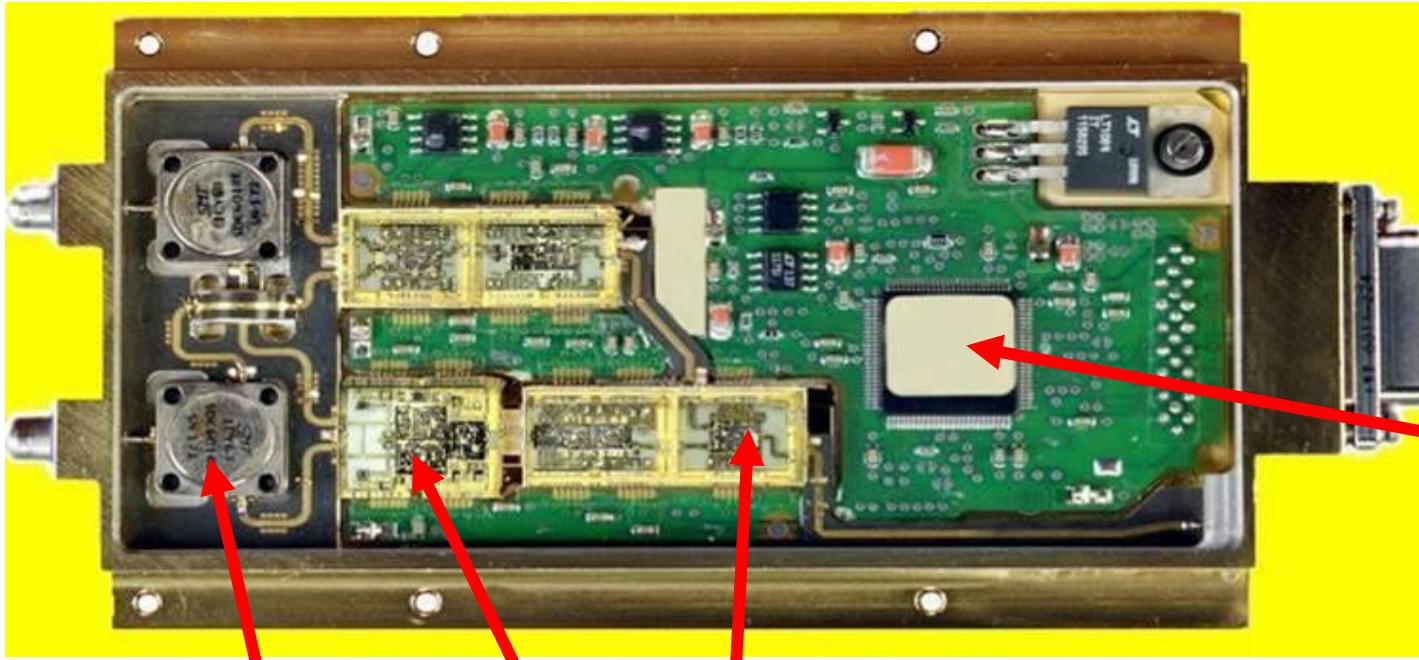


Phase shifter a  
componenti discreti  
(scarsamente ripetibili)

- Tecnologia ibrida con MMIC e stadi RF avvitati in cavità
- Driver di controllo dedicati ad ogni stadio
- Assenza di scheda di controllo con logica programmabile
- Utilizzo di Switch a diodi per la commutazione RX-TX

# Tx/Rx 2° Generation

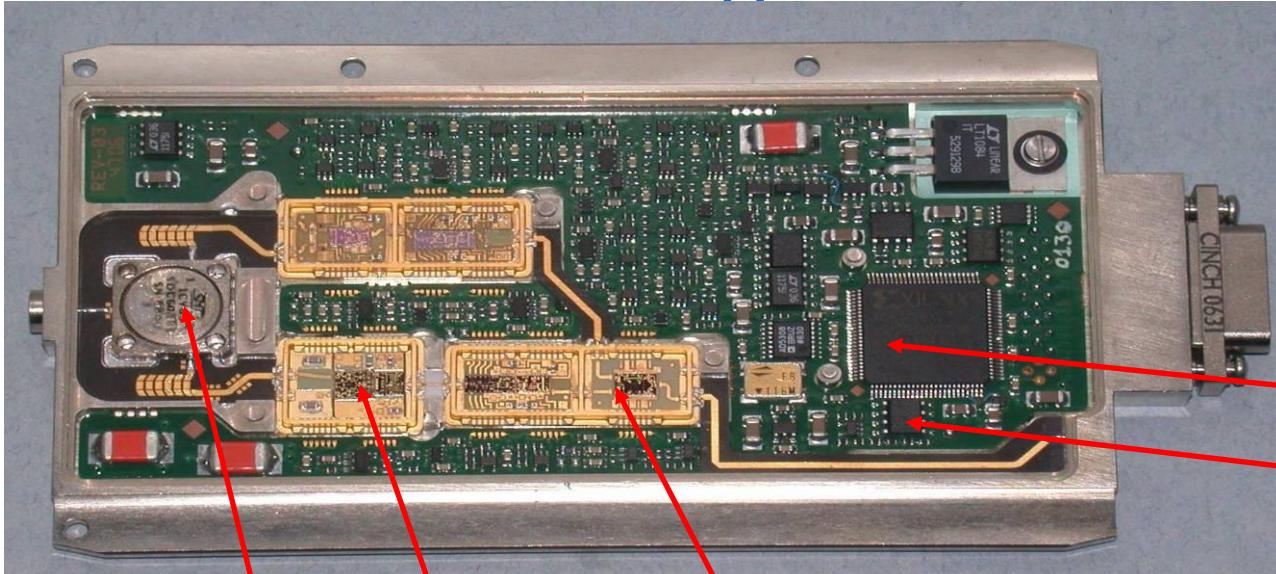
## TXRX 4Watt RFout - Naval Application



- Tecnologia con micro-package per alloggiare il Chipset di MMIC
- 2 Circolatori 6-18GHz per isolamento RX-TX e doppia polarizzazione
- Phase Shifter in tecnologia MMIC

# Tx/Rx 2° Generation

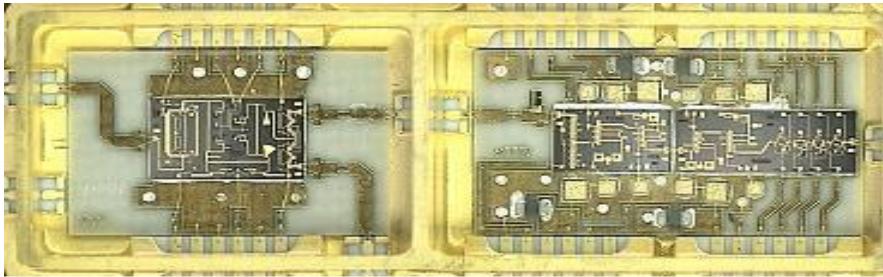
## TXRX RFout - Avionic Application



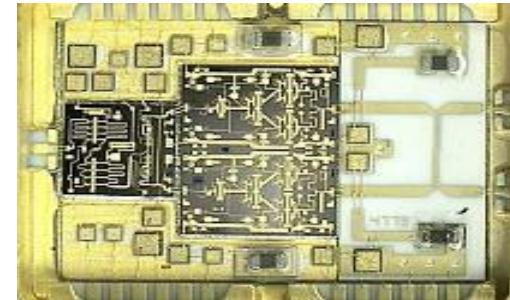
PLD e E<sup>2</sup>Prom con DAC esterni  
per la scheda controlli

Tecnologia con micro-package per alloggiare il Chipset di MMIC  
Impiego del circolatore 6-18GHz per isolamento RX-TX  
Scheda con logica programmabile e controllo in temperatura

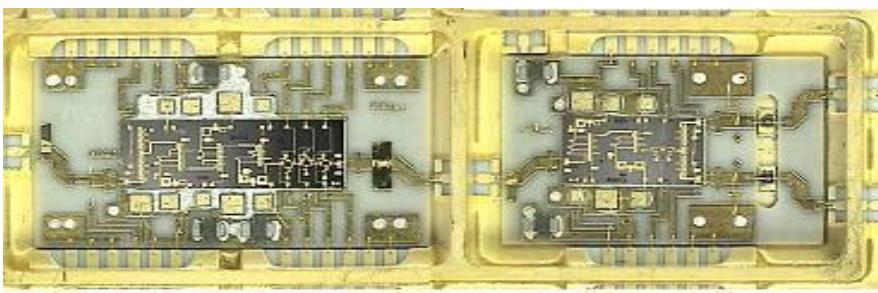
# Multichip Packaging for High Integration T/R Module



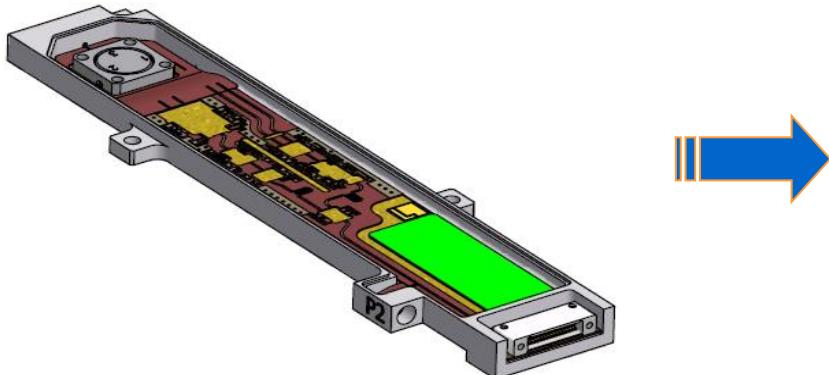
- More than 30dB gain
- Hermetically sealed sub-assemblies



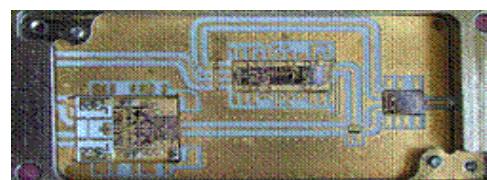
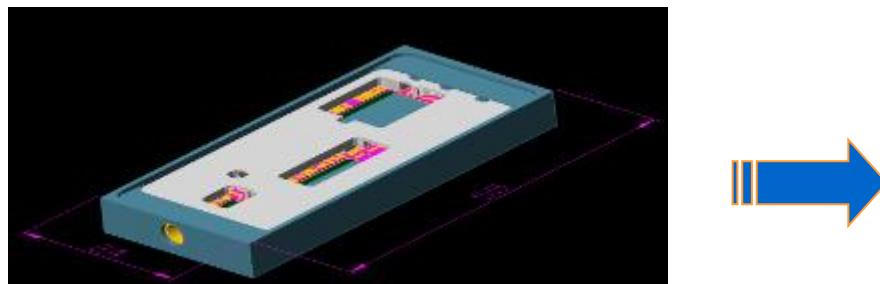
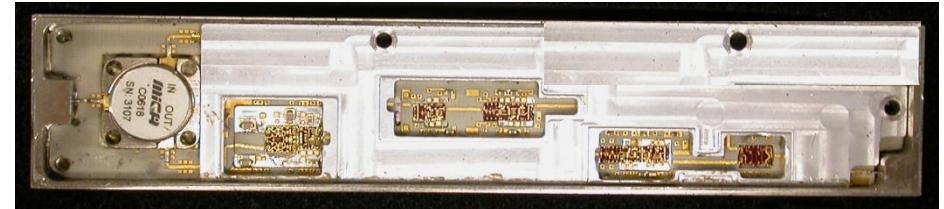
- $\text{Cu}_{20}\text{Mo}_{80}$  heat spreaders
- Microstrip-stripline-microstrip for RF I/O transitions
- Epoxy glued or brazed MMIC for best thermal dissipation;
- Internal bypass capacitors
- Automatic assembling compatible



# Tx / Rx – 3° generation of TR modules



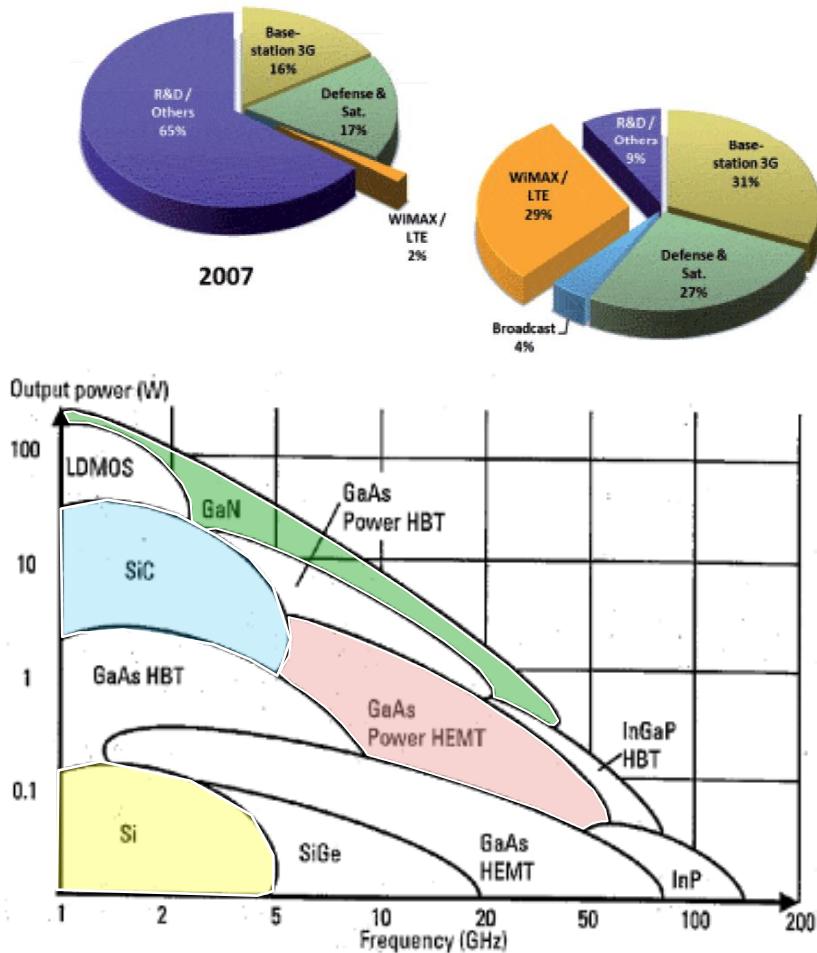
First prototype



Multilayer Technology - RF and Digital circuit integrated on the same substrate.

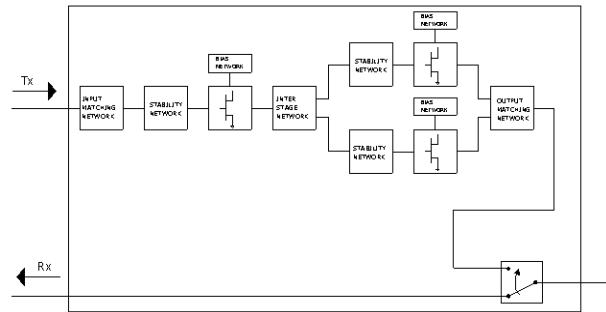
# Gallium Arsenide (GaAs) VS Gallium Nitride (GaN)

Parameter	Unit	SiC	Si	GaAs (AlGaAs/InGaAs)	GaN (AlGaN/GaN)
BandGap Energy	eV	3.26	1.12	1.43	3.44
Electric breakdown field	MV/cm	3	0.3	0.4	3.0
Saturated (peak) electrons velocity	x10 <sup>7</sup> cm/s	2.0 (2.0)	1.0 (1.0)	1.0 (2.1)	2.5 (2.7)
Electron mobility	cm <sup>2</sup> /V·s	700	1500	8500	1000-2000
Thermal conductivity	W/cm·K	3.7 – 4.5	1.5	0.5	1.3 – 2.1
Relative permittivity	-	10.1	11.8	12.8	9.0

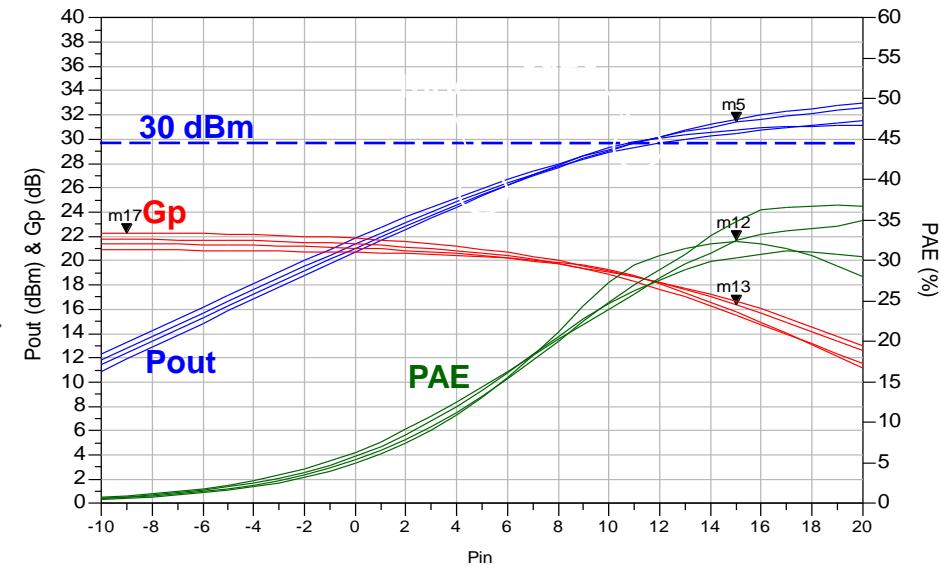


# Why GaN Technology ?

- *High voltage supply (>30V)*
- *High current density;*
- *High power density; (>3W/mm)*
- *Efficiency;*
- *Thermal management;*
- *Survivability*



- *Pout 1W;*
- *High Efficiency: 33% average;*
- *High small signal gain: 20 dB;*
- *No drivers;*
- *Robust SPDT instead of ferrite circulators;*
- *Size: 3x4 mm.*

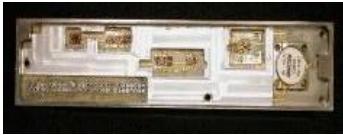


# Innovation and applications of GaN - 4° generation of TR modules

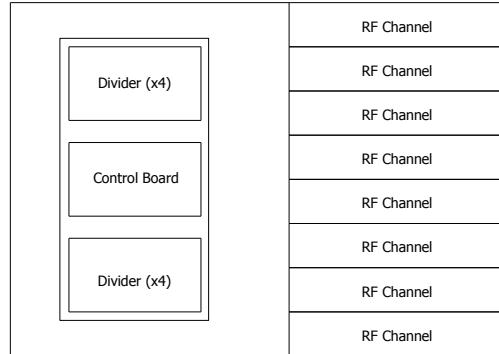
## T/R modules



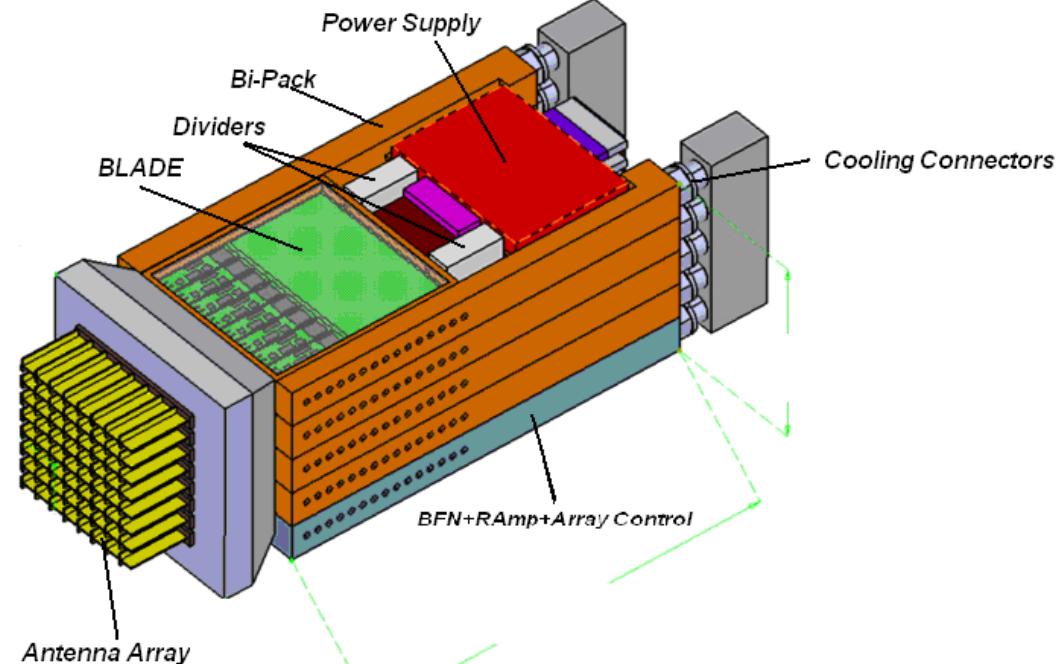
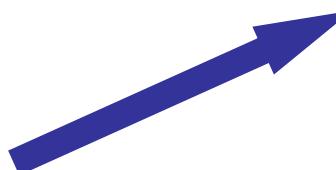
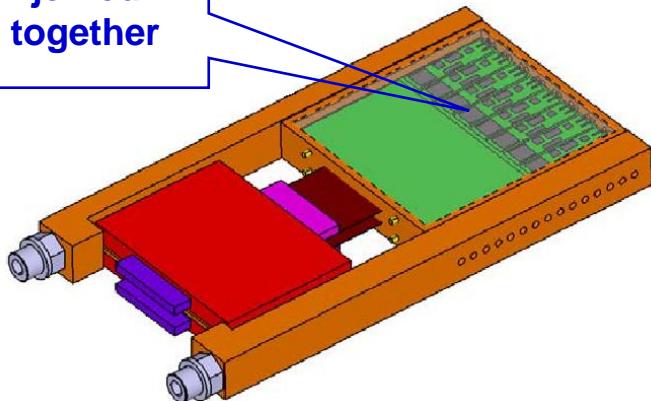
...x8...



VS



8 T/R  
joined together



- MMIC Size reduction: 60 %
- Cost reduction: 60 %
- Efficiency increase: 90 %
- Cooling system lighter
- Losses reduction versus antennas

# MICROELECTRONICS CLEAN ROOM AREAS



# AUTOMATIC TEST AREA





## ENVIRONMENTAL TEST AREA



**www\_elt-roma\_com**

### Lettura di riferimento

- Microwave Receivers With Electronic Warfare Applications, James Tsui, WILEY
- Integrated Microwave Front-Ends with Avionics Applications, Leo G. Maloratsky, ARTECH HOUSE RADAR LIBRARY
- Fundamentals of Electronic Warfare, Sergei A. Vakin, Lev N. Shustov, Robert H. Dunwell, ARTECH HOUSE RADAR LIBRARY
- EW 101: A First Course in Electronic Warfare, David L. Adamy, ARTECH HOUSE RADAR LIBRARY
- EW 102: A Second Course in Electronic Warfare, David L. Adamy, ARTECH HOUSE RADAR LIBRARY
- EW 103: Tactical Battlefield Communications Electronic Warfare, David L. Adamy, ARTECH HOUSE RADAR LIBRARY